Vishay Semiconductors

# Thyristor High Voltage, Phase Control SCR, 30 A



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| PRIMARY CHARACTERISTICS            |                   |  |  |  |  |  |  |
|------------------------------------|-------------------|--|--|--|--|--|--|
| I <sub>T(AV)</sub>                 | 20 A              |  |  |  |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | 800 V, 1200 V     |  |  |  |  |  |  |
| V <sub>TM</sub>                    | 1.3 V             |  |  |  |  |  |  |
| I <sub>GT</sub>                    | 45 mA             |  |  |  |  |  |  |
| TJ                                 | -40 °C to +125 °C |  |  |  |  |  |  |
| Package                            | TO-247AC 3L       |  |  |  |  |  |  |
| Circuit configuration              | Single SCR        |  |  |  |  |  |  |

### **FEATURES**

- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **APPLICATIONS**

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding and battery charge

### DESCRIPTION

The VS-30TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

| PARAMETER                          | TEST CONDITIONS              | VALUES      | UNITS |  |  |
|------------------------------------|------------------------------|-------------|-------|--|--|
| I <sub>T(AV)</sub>                 | Sinusoidal waveform          | 20          | ^     |  |  |
| I <sub>RMS</sub>                   |                              | 30          | - A   |  |  |
| V <sub>RRM</sub> /V <sub>DRM</sub> |                              | 800 to 1200 | V     |  |  |
| I <sub>TSM</sub>                   |                              | 300         | A     |  |  |
| V <sub>T</sub>                     | 20 A, T <sub>J</sub> = 25 °C | 1.3         | V     |  |  |
| dV/dt                              |                              | 500         | V/µs  |  |  |
| dl/dt                              |                              | 150         | A/µs  |  |  |
| TJ                                 |                              | -40 to +125 | °C    |  |  |

| VOLTAGE RATINGS |   |   |   |  |  |  |  |  |  |  |
|-----------------|---|---|---|--|--|--|--|--|--|--|
| PART NUMBER     | V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM<br>REPETITIVE PEAK AND<br>OFF-STATE VOLTAGE<br>V | V <sub>RSM</sub> , MAXIMUM<br>NON-REPETITIVE PEAK<br>REVERSE VOLTAGE<br>V | I <sub>RRM</sub> /I <sub>DRM</sub><br>AT 125 °C<br>mA |  |  |  |  |  |  |  |
| VS-30TPS08-M3   | 800   | 900   | 10  |  |  |  |  |  |  |  |
| VS-30TPS12-M3   | 1200  | 1300  | 10  |  |  |  |  |  |  |  |



# VS-30TPS..-M3 Series



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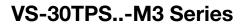
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| ABSOLUTE MAXIMUM RATING                   | S                                |  |  |        |                  |  |
|---|----------------------------------|--|--|--------|------------------|--|
| PARAMETER                                 | SYMBOL                           | TEST CO  | NDITIONS                               | VALUES | UNITS            |  |
| Maximum average on-state current          | I <sub>T(AV)</sub>               | $T_{\rm C}$ = 95 °C, 180° conduction                                   | half sine wave                         | 20     |                  |  |
| Maximum RMS on-state current              | I <sub>RMS</sub>                 |  |  | 30     | А                |  |
| Maximum peak, one-cycle                   |                                  | 10 ms sine pulse, rated $V_{RRN}$                                      | <sub>A</sub> applied                   | 250    | A                |  |
| non-repetitive surge current              | I <sub>TSM</sub>                 | 10 ms sine pulse, no voltage   | 10 ms sine pulse, no voltage reapplied |        |                  |  |
| Maximum I <sup>2</sup> t for fusing       | l <sup>2</sup> t                 | 10 ms sine pulse, rated $V_{RRM}$                                      | <sub>A</sub> applied                   | 310    | A <sup>2</sup> s |  |
| Maximum - t for fusing                    | 1-1                              | 10 ms sine pulse, no voltage   | 442                                    | A-5    |                  |  |
| Maximum I²√t for fusing                   | l²√t                             | t = 0.1 to 10 ms, no voltage   | 4420                                   | A²√s   |                  |  |
| Maximum on-state voltage drop             | V <sub>TM</sub>                  | 20 A, T <sub>J</sub> = 25 °C   | 1.3                                    | V      |                  |  |
| On-state slope resistance                 | r <sub>t</sub>                   | T 125 °C   |  | 12     | mΩ               |  |
| Threshold voltage                         | V <sub>T(TO)</sub>               | T <sub>J</sub> = 125 °C  |  | 1.0    | V                |  |
| Maximum reverse and direct leakage        | 1/1                              | T <sub>J</sub> = 25 °C   | $V_{R} = rated V_{RRM}/V_{DRM}$        | 0.5    |                  |  |
| current                                   | I <sub>RM</sub> /I <sub>DM</sub> | T <sub>J</sub> = 125 °C  | VR = Tated VRRM/ VDRM                  | 10     | mA               |  |
| Maximum holding current                   | Ι <sub>Η</sub>                   | Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C |  |        | ША               |  |
| Maximum latching current                  | ١L                               | Anode supply = 6 V, resistive load, $T_J$ = 25 °C                      |  |        |                  |  |
| Maximum rate of rise of off-state voltage | dV/dt                            | $T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$ -k = open        |  |        | V/µs             |  |
| Maximum rate of rise of turned-on current | dl/dt                            |  |  | 150    | A/µs             |  |

| TRIGGERING                                     |                    |  |        |       |  |
|--|--------------------|--|--------|-------|--|
| PARAMETER                                      | SYMBOL             | TEST CONDITIONS  | VALUES | UNITS |  |
| Maximum peak gate power                        | P <sub>GM</sub>    |  | 8.0    | W     |  |
| Maximum average gate power                     | P <sub>G(AV)</sub> |  | 2.0    | vv    |  |
| Maximum peak positive gate current             | + I <sub>GM</sub>  |  | 1.5    | А     |  |
| Maximum peak negative gate voltage             | - V <sub>GM</sub>  |  | 10     | V     |  |
|  |                    | Anode supply = 6 V, resistive load, $T_J$ = -10 °C                 | 60     | 0     |  |
| Maximum required DC gate current to<br>trigger | I <sub>GT</sub>    | $I_{GT}$ Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$ |        | mA    |  |
|  |                    | Anode supply = 6 V, resistive load, $T_J$ = 125 °C                 | 20     |       |  |
|  |                    | Anode supply = 6 V, resistive load, $T_J$ = -10 °C                 | 2.5    |       |  |
| Maximum required DC gate<br>voltage to trigger | V <sub>GT</sub>    | Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$          | 2.0    | v     |  |
|  |                    | Anode supply = 6 V, resistive load, $T_J$ = 125 °C                 | 1.0    | v     |  |
| Maximum DC gate voltage not to trigger         | V <sub>GD</sub>    | T 105 °C V reteducture   | 0.25   |       |  |
| Maximum DC gate current not to trigger         | I <sub>GD</sub>    | $T_J = 125 \text{ °C}, V_{DRM} = \text{rated value}$               | 2.0    | mA    |  |

| SWITCHING                     |                 |                         |        |       |  |  |  |  |  |
|-------------------------------|-----------------|-------------------------|--------|-------|--|--|--|--|--|
| PARAMETER                     | SYMBOL          | TEST CONDITIONS         | VALUES | UNITS |  |  |  |  |  |
| Typical turn-on time          | t <sub>gt</sub> | $T_J = 25 \text{ °C}$   | 0.9    |       |  |  |  |  |  |
| Typical reverse recovery time | t <sub>rr</sub> | T <sub>1</sub> = 125 °C | 4      | μs    |  |  |  |  |  |
| Typical turn-off time         | tq              | 1] = 125 C              | 110    |       |  |  |  |  |  |

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| THERMAL AND MECHANICAL SPECIFICATIONS           |                |                      |                                      |             |            |  |  |  |  |
|---|----------------|----------------------|--------------------------------------|-------------|------------|--|--|--|--|
| PARAMETER                                       |                | SYMBOL               | YMBOL TEST CONDITIONS                |             | UNITS      |  |  |  |  |
| Maximum junction and storage temperature range  |                | TJ, T <sub>Stg</sub> |                                      | -40 to +125 | °C         |  |  |  |  |
| Maximum thermal resistance, junction to case    |                | R <sub>thJC</sub>    | DC operation                         | 0.8         |            |  |  |  |  |
| Maximum thermal resistance, junction to ambient |                | R <sub>thJA</sub>    |                                      |             | °C/W       |  |  |  |  |
| Maximum thermal resistance, case to heatsink    |                | R <sub>thCS</sub>    | Mounting surface, smooth and greased | 0.2         |            |  |  |  |  |
| Approximate weight                              |                |                      |                                      | 6           | g          |  |  |  |  |
| Approximate weight                              |                |                      |                                      | 0.21        | oz.        |  |  |  |  |
| Mounting torque                                 | minimum        |                      |                                      | 6 (5)       | kgf · cm   |  |  |  |  |
| Mounting torque                                 | maximum        |                      |                                      | 12 (10)     | (lbf ⋅ in) |  |  |  |  |
|   |                |                      |                                      | 30TPS08     |            |  |  |  |  |
| warking device                                  | Marking device |                      | Case style TO-247AC 3L               | 30TPS12     |            |  |  |  |  |

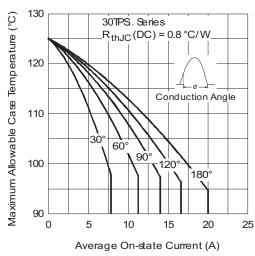
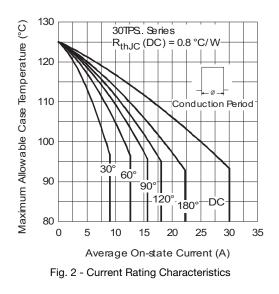


Fig. 1 - Current Rating Characteristics



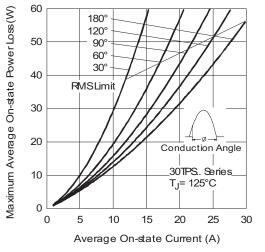
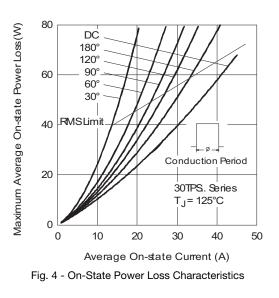


Fig. 3 - On-State Power Loss Characteristics



Revision: 26-Feb-2019

3

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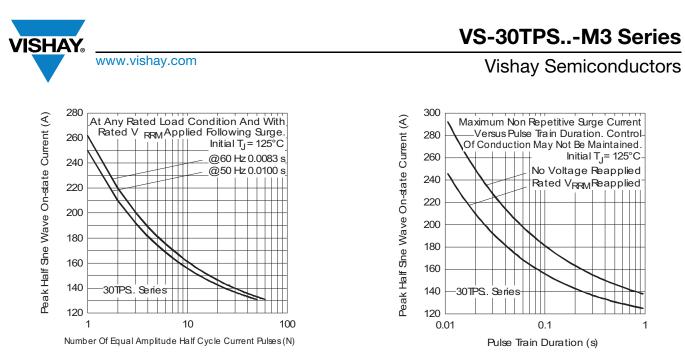
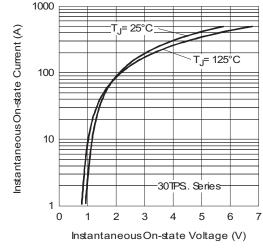
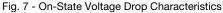
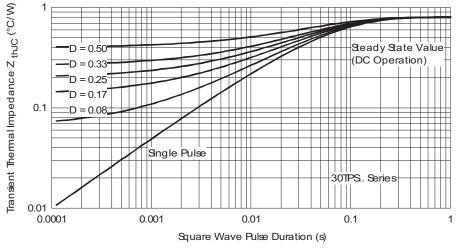




Fig. 6 - Maximum Non-Repetitive Surge Current





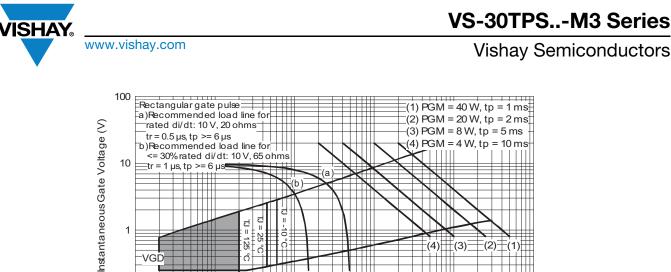




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 4
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Frequency Limited by PG(AV)

10

100

Instantaneous Gate Current (A)

1

Fig. 9 - Gate Characteristics

30TPS. Series

0.1

### **ORDERING INFORMATION TABLE**

1

0.1 0.001

VGD

IGD

0.01

| Device code | VS-               | 30         | т                           | Р                    | s       | 12    | -M3 |                                     |
|-------------|-------------------|------------|-----------------------------|----------------------|---------|-------|-----|-------------------------------------|
|             |                   | 2          | 3                           | 4                    | 5       | 6     | 7   |                                     |
|             | 1 -<br>2 -<br>3 - | Cur        | rent rati                   | iiconduc<br>ng (30 = | : 30 A) | oduct |     |                                     |
|             | 4 -               | T =<br>Pac | thyristo<br>kage:<br>TO-247 | r                    |         |       |     |                                     |
|             | 5 -               | Typ<br>S = | e of silio<br>standar       |                      | •       |       |     | B = 800 V                           |
|             | 7 -               | Envi       | ronmen                      | tal digit:           |         |       |     | = 1200 V<br>terminations lead (Pb)- |

| ORDERING INFORMATION (Example) |                  |                        |                          |  |  |  |  |  |  |
|--------------------------------|------------------|------------------------|--------------------------|--|--|--|--|--|--|
| PREFERRED P/N                  | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION    |  |  |  |  |  |  |
| VS-30TPS08-M3                  | 25               | 500                    | Antistatic plastic tubes |  |  |  |  |  |  |
| VS-30TPS12-M3                  | 25               | 500                    | Antistatic plastic tubes |  |  |  |  |  |  |

| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?96138 |  |  |  |  |  |
| Part marking information   | www.vishay.com/doc?95007 |  |  |  |  |  |

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TO-247AC 3L

### **DIMENSIONS** in millimeters and inches



| SYMBOL  | MILLIMETERS |       | INC   | HES   | NOTES | NOTES |        | MILLIN | IETERS | INC   | HES   | NOTES |
|---------|-------------|-------|-------|-------|-------|-------|--------|--------|--------|-------|-------|-------|
| STWIDOL | MIN.        | MAX.  | MIN.  | MAX.  | NOTES |       | SYMBOL | MIN.   | MAX.   | MIN.  | MAX.  | NOTES |
| A       | 4.65        | 5.31  | 0.183 | 0.209 |       |       | D2     | 0.51   | 1.35   | 0.020 | 0.053 |       |
| A1      | 2.21        | 2.59  | 0.087 | 0.102 |       |       | E      | 15.29  | 15.87  | 0.602 | 0.625 | 3     |
| A2      | 1.17        | 1.37  | 0.046 | 0.054 |       |       | E1     | 13.46  | -      | 0.53  | -     |       |
| b       | 0.99        | 1.40  | 0.039 | 0.055 |       |       | е      | 5.46   | BSC    | 0.215 | 5 BSC |       |
| b1      | 0.99        | 1.35  | 0.039 | 0.053 |       |       | ØК     | 0.2    | 254    | 0.0   | )10   |       |
| b2      | 1.65        | 2.39  | 0.065 | 0.094 |       |       | L      | 14.20  | 16.10  | 0.559 | 0.634 |       |
| b3      | 1.65        | 2.34  | 0.065 | 0.092 |       |       | L1     | 3.71   | 4.29   | 0.146 | 0.169 |       |
| b4      | 2.59        | 3.43  | 0.102 | 0.135 |       |       | ØΡ     | 3.56   | 3.66   | 0.14  | 0.144 |       |
| b5      | 2.59        | 3.38  | 0.102 | 0.133 |       |       | Ø P1   | -      | 7.39   | -     | 0.291 |       |
| С       | 0.38        | 0.89  | 0.015 | 0.035 |       |       | Q      | 5.31   | 5.69   | 0.209 | 0.224 |       |
| c1      | 0.38        | 0.84  | 0.015 | 0.033 |       |       | R      | 4.52   | 5.49   | 0.178 | 0.216 |       |
| D       | 19.71       | 20.70 | 0.776 | 0.815 | 3     |       | S      | 5.51   | BSC    | 0.217 | ' BSC |       |
| D1      | 13.08       | -     | 0.515 | -     | 4     |       |        |        |        |       |       |       |

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension Q

Revision: 20-Jun-17

1



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